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- 1 [20070117360](#) Isolated vertical power device structure with both N-doped and P-doped trenches
- 2 [20070035906](#) Transient blocking unit
- 3 [20070012999](#) Method for Making a Semiconductor Device Including Regions of Band-Engineered Semiconductor Superlattice to Reduce Device-On Resistance
- 4 [20070012983](#) Terminations for semiconductor devices with floating vertical series capacitive structures
- 5 [20070012911](#) Semiconductor Device Including Regions of Band-Engineered Semiconductor Superlattice to Reduce Device-On Resistance
- 6 [20060292889](#) FINFET Including a Superlattice
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- 8 [20060267083](#) Power semiconductor device having a voltage sustaining region that includes doped columns formed with a single ion implantation step
- 9 [20060261407](#) High-voltage transistor fabrication with trench etching technique
- 10 [20060249788](#) High voltage power MOSFET having low on-resistance
- 11 [20060238936](#) Apparatus and method for transient blocking employing relays
- 12 [20060231857](#) METHOD FOR MAKING A SEMICONDUCTOR DEVICE INCLUDING A MEMORY CELL WITH A NEGATIVE DIFFERENTIAL RESISTANCE (NDR) DEVICE
- 13 [20060226502](#) Microelectromechanical Systems (MEMS) Device Including a Superlattice
- 14 [20060223215](#) Method for Making a Microelectromechanical Systems (MEMS) Device Including a Superlattice
- 15 [20060202189](#) SEMICONDUCTOR DEVICE INCLUDING A MEMORY CELL WITH A NEGATIVE DIFFERENTIAL RESISTANCE (NDR) DEVICE

16 20060163690 Semiconductor having thick dielectric regions
17 20060134867 Technique for forming the deep doped columns in superjunction
18 20060131605 Low capacitance two-terminal barrier controlled TVS diodes
19 20060125003 High voltage power MOSFET having low on-resistance
20 20060008937 Technique for fabricating multilayer color sensing photodetectors
21 20050189586 DMOS device with a programmable threshold voltage
22 20050139914 Method for forming thick dielectric regions using etched trenches
23 20050110110 Integrated released beam layer structure fabricated in trenches and manufacturing method thereof
24 20050095789 Trench DMOS transistor structure having a low resistance path to a drain contact located on an upper surface
25 20050054136 Fabrication of diaphragms and "floating" regions of single crystal semiconductor for MEMS devices
26 20050042830 High voltage power MOSFET having a voltage sustaining region that includes Doped Columns Formed by trench etching and diffusion from regions of oppositely doped polysilicon
27 20050001272 MOSFET device having geometry that permits frequent body contact
28 20040251917 Capacitive sensor device with electrically configurable pixels
29 20040235250 Symmetric trench MOSFET device and method of making same
30 20040178444 Double diffused field effect transistor having reduced on-resistance
31 20040175855 TECHNIQUE FOR FABRICATING MEMS DEVICES HAVING DIAPHRAGMS OF "FLOATTING" REGIONS OF SINGLE CRYSTAL MATERIAL
32 20040164348 High voltage power mosfet having a voltage sustaining region that includes doped columns formed by trench etching using an etchant gas that is also a doping source
33 20040157384 Power semiconductor device having a voltage sustaining region that includes doped columns formed with a single ion implantation step
34 20040124960 Integrated circuit inductors using driven shields
35 20040110333 High voltage power MOSFET having a voltage sustaining region that includes doped columns formed by trench etching and ion implantation
36 20040097028 Method for fabricating a power semiconductor device having a voltage sustaining layer with a terraced trench facilitating formation of floating islands
37 20040070044 High voltage power MOSFET having low on-resistance
38 20040036138 High voltage power MOSFET having low on-resistance
39 20040032762 DMOS device with a programmable threshold voltage
40 20040031989 TWO TERMINAL PROGRAMMABLE MOS-GATED CURRENT SOURCE
41 20040009643 METHOD FOR FABRICATING A HIGH VOLTAGE POWER MOSFET HAVING A VOLTAGE SUSTAINING REGION THAT INCLUDES DOPED COLUMNS FORMED BY RAPID DIFFUSION
42 20030211671 SURFACE GEOMETRY FOR A MOS-GATED DEVICE THAT ALLOWS THE MANUFACTURE OF DICE HAVING DIFFERENT SIZES
43 20030209766 Method for using a surface geometry for a MOS-gated device in the manufacture of dice having different sizes
44 20030209759 MOSFET DEVICE HAVING GEOMETRY THAT PERMITS FREQUENT BODY CONTACT

45	<u>20030203552</u>	High voltage power MOSFET having a voltage sustaining region that includes doped columns formed by trench etching and diffusion from regions of oppositely doped polysilicon
46	<u>20030181010</u>	<u>POWER SEMICONDUCTOR DEVICE HAVING A VOLTAGE SUSTAINING REGION THAT INCLUDES DOPED COLUMNS FORMED WITH A SINGLE ION IMPLANTATION STEP</u>
47	<u>20030173581</u>	Photodiode stacks for photovoltaic relays and the method of manufacturing the same
48	<u>20030122189</u>	High voltage power MOSFET having a voltage sustaining region that includes doped columns formed by trench etching using an etchant gas that is also a doping source
49	<u>20030122188</u>	High voltage power MOSFET having a voltage sustaining region that includes doped columns formed by trench etching and ion implantation
50	<u>20030075729</u>	Minimum sized cellular MOS-gated device geometry

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51 20030068863	Method for fabricating a power semiconductor device having a floating island voltage sustaining layer
52 20030068854	Method for fabricating a power semiconductor device having a voltage sustaining layer with a terraced trench facilitating formation of floating Islands
53 20030040144	Trench DMOS transistor with embedded trench schottky rectifier
54 20020195655	Symmetric trench MOSFET device and method of making same
55 20020140028	Double diffused field effect transistor having reduced on-resistance
56 20020140025	High voltage power MOSFET having low on-resistance
57 20020132432	Field effect transistor having dielectrically isolated sources and drains and method for making same
58 20020125527	Trench DMOS transistor structure having a low resistance path to a drain contact located on an upper surface
59 20020066924	High voltage power MOSFET having low on-resistance
60 20020017684	Transistor with integrated photodetector for conductivity modulation
61 20020014658	High voltage power mosfet having low on-resistance
62 20020009832	Method of fabricating high voltage power mosfet having low on-resistance
63 20010028578	Method and apparatus for providing an embedded flash-EEPROM technology
64 20010028085	Trench DMOS transistor structure having a low resistance path to a drain contact located on an upper surface
65 20010000111	Field effect transistor having dielectrically isolated sources and drains and method for making same

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